

AMENDMENTS TO THE ABSTRACT OF DISCLOSURE

Please replace the Abstract of the Disclosure with the following amended Abstract of the Disclosure:

ABSTRACT OF THE DISCLOSURE

A semiconductor memory device, including a first memory cell having a first gate electrode, a first diffusion layer and a second diffusion layer, ~~the first and second diffusion layers arranged in a semiconductor substrate to be adjacent to the first gate electrode~~; a first contact layer connected to the first diffusion layer of the first memory cell; a second contact layer connected to the first contact layer; ~~a first bit line connected to the second contact layer and arranged above the first gate electrode of the first memory cell~~; a second memory cell having a second gate electrode, a third diffusion layer and a fourth diffusion layer, ~~the third and fourth diffusion layers arranged in a semiconductor substrate to be adjacent to the second gate electrode~~, the second gate electrode of the second memory cell electrically connected to the first gate electrode of the first memory cell, the first and second memory cells arranged in a direction perpendicular to the first bit line; ~~a second bit line connected to the third diffusion layer, arranged above the second gate electrode of the second memory cell, and arranged parallel to the first bit line~~; and a conductive layer commonly connected to the second diffusion layer of the first memory cell and the fourth diffusion layer of the second memory cell, a height of the conductive layer substantially being coplanar with a height of the first contact layer.